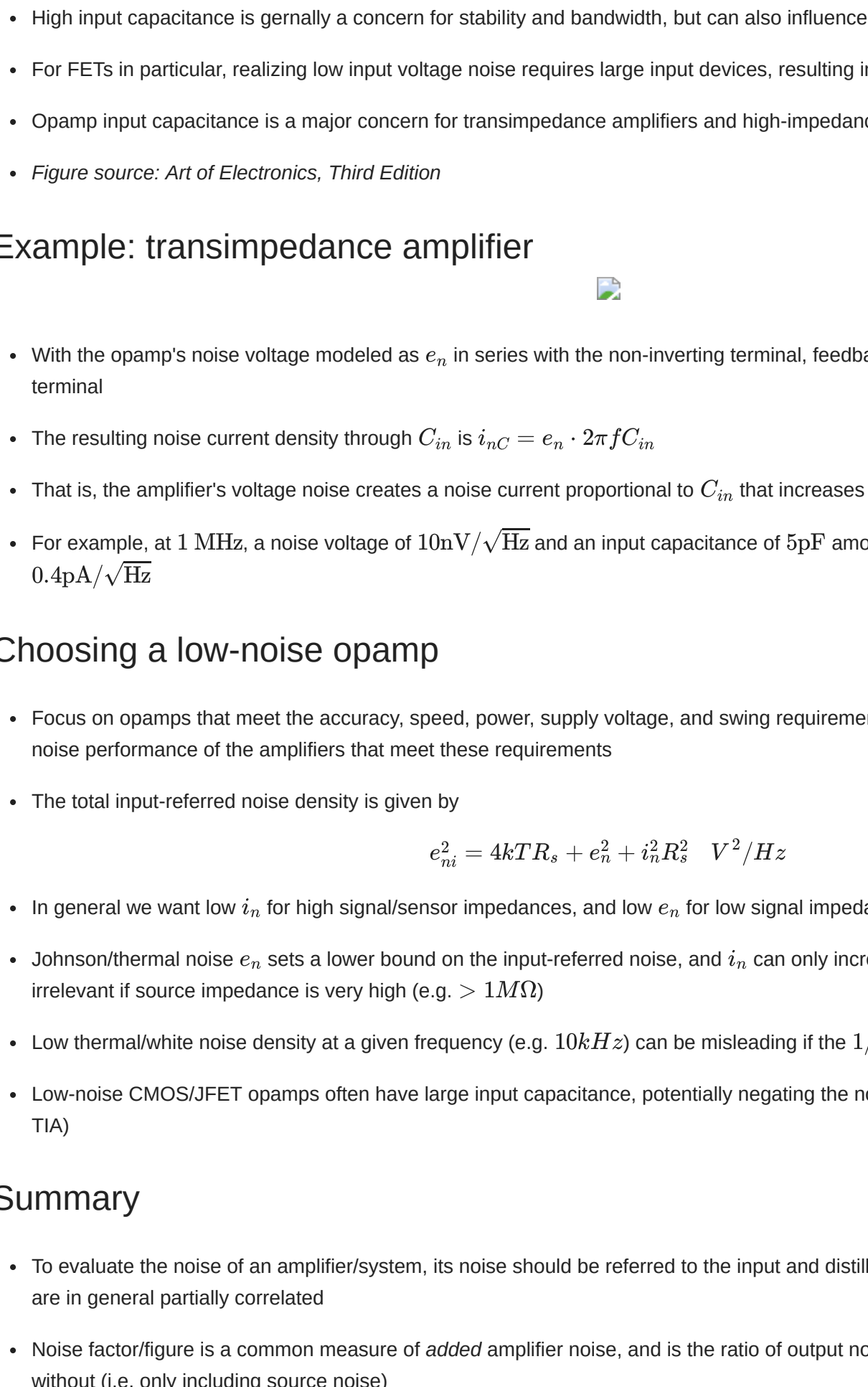


- The impact of f_c is on integrated noise, with higher values leading to substantially more RMS noise and lower frequencies
- Again, the integrated noise curves converge at frequencies beyond the amplifiers' respective values of f_c

```
In [358]: plot_log3xy(f, 1e6*vn1_rms, 1e6*vn2_rms, 1e6*vn3_rms, 'Bandwidth [Hz]', r'RMS Voltage Noise [5\u03bcV]',  
               r'$f_c = 100Hz$', r'$f_c = 1kHz$', r'$f_c=10kHz$')
```



Input capacitance



- High input capacitance is gernaly a concern for stability and bandwidth, but can also influence noise performance
- For FETs in particular, realizing low input voltage noise requires large input devices, resulting in high values of input capacitance C_{in}
- Opamp input capacitance is a major concern for transimpedance amplifiers and high-impedance sensor applications
- Figure source: *Art of Electronics, Third Edition*

Example: transimpedance amplifier



- With the opamp's noise voltage modeled as e_n in series with the non-inverting terminal, feedback forces e_n to appear at the inverting terminal
- The resulting noise current density through C_{in} is $i_{nC} = e_n \cdot 2\pi f C_{in}$
- That is, the amplifier's voltage noise creates a noise current proportional to C_{in} that increases with frequency
- For example, at 1 MHz, a noise voltage of $10nV/\sqrt{Hz}$ and an input capacitance of 5pF amount to a noise current density of $0.4pA/\sqrt{Hz}$

Choosing a low-noise opamp

- Focus on opamps that meet the accuracy, speed, power, supply voltage, and swing requirements of the application, and evaluate the noise performance of the amplifiers that meet these requirements
- The total input-referred noise density is given by

$$e_{ni}^2 = 4kTR_s + e_n^2 + i_n^2 R_s^2 \quad V^2/Hz \tag{37}$$

- In general we want low i_n for high signal/sensor impedances, and low e_n for low signal impedances
- Johnson/thermal noise e_n sets a lower bound on the input-referred noise, and i_n can only increase it. Low voltage noise is often irrelevant if source impedance is very high (e.g. $> 1M\Omega$)
- Low thermal/white noise density at a given frequency (e.g. $10kHz$) can be misleading if the $1/f$ corner is high
- Low-noise CMOS/JFET opamps often have large input capacitance, potentially negating the noise benefit for certain applications (e.g. TIA)

Summary

- To evaluate the noise of an amplifier/system, its noise should be referred to the input and distilled into two sources, e_n and i_n , which are in general partially correlated
- Noise factor/figure is a common measure of added amplifier noise, and is the ratio of output noise with the opamp's internal noise and without (i.e. only including source noise)
- Input-referred noise includes e_n and i_n , in addition to the noise due to the source, e_s , and should be used to evaluate the "raw" noise performance of a given design
- For most applications, integrated (RMS) noise is more relevant than spot noise (though the latter will inform the former)